

## INFORMATION DISCLOSURE CITATION

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## U.S. PATENT DOCUMENTS

Examiner Initial*	Document Number	Issue Date	Name	Class	Sub Class	Filing Date If Appropriate

## FOREIGN PATENT DOCUMENTS

Document Number	Publication Date	Country	Class	Sub Class	Translation Yes or No

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

WB	YASUDA, Y. et al., "Radical Nitridation in Multi-Oxide Process for 100nm Generation CMOS Technology", 2001 Symposium on VLSI Technology Digest of Technical Papers, 2 pages, (2001).
WB	CHEN, C. H. et al., "Downscaling Limit of Equivalent Oxide Thickness in Formation of Ultrathin Gate Dielectric by Thermal-Enhanced Remote Plasma Nitridation", IEEE Transactions on Electron Devices, Vol. 49, No. 5, pp. 840-846, (May 2002).

Examiner	<i>William M. Brewster</i>	Date Considered	1 FEB 06
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